

Silicon Switching Diode

1N4150
or
1N4150-1

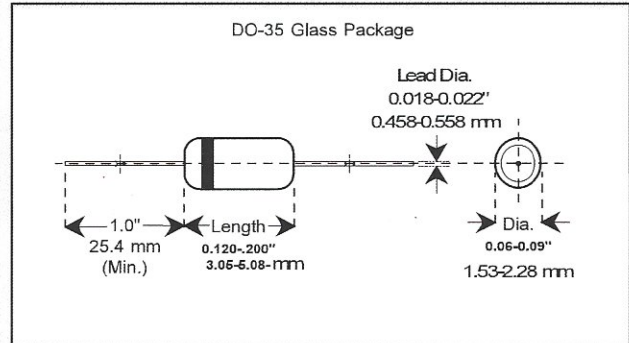
DO-35 Glass Package

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- LL-34/35 MELF SMD available
- Full approval to Mil-S-19500/231
- Available up to JANTXV-1 levels
- "S" level screening available to Source Control Drawings



Maximum Ratings	Symbol	Value	Unit	
Peak Inverse Voltage	PV	75 (Min)	Volts	
Average Rectified Current	I_{Avg}	200	mAmps	
Continuous Forward Current	I_{Fdc}	400	mAmps	
Peak Surge Current ($t_{peak} = 1$ sec.)	I_{peak}	0.5	Amp	
BKC Power Dissipation $T_L = 50$ °C, $L = 3/8$ " from body	P_{tot}	500	mWatts	
Operating Temperature Range	T_{Op}	-65 to +200	°C	
Storage Temperature Range	T_{St}	-65 to +200	°C	
Electrical Characteristics @ 25 °C	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ $I_F = 1.0$ mA	V_F	0.54	0.62	Volts
Forward Voltage Drop @ $I_F = 10$ mA	V_F	0.66	0.74	Volts
Forward Voltage Drop @ $I_F = 50$ mA	V_F	0.76	0.86	Volts
Forward Voltage Drop @ $I_F = 100$ mA	V_F	0.80	0.92	Volts
Forward Voltage Drop @ $I_F = 200$ mA	V_F	0.87	1.0	Volts
Reverse Leakage Current @ $V_R = 50$ V	I_R		0.1 (100 @ 150 °C)	µA
Breakdown Voltage @ $I_R = 0.1$ mA	PIV	75		Volts
Capacitance @ $V_R = 0$ V, $f = 1$ kHz	C_T		2.5	pF
Reverse Recovery time (note 1)	t_{rr}		4.0	nSecs
Reverse Recovery time (note 2,3)	t_{rr}		6.0	nSecs
Forward Recovery time (note 4)	V_{fr}		10	nSecs

Note 1: Per Method 4031-A with $I_F = I_R = 10$ to 200 mA, $R_L = 100$ Ohms, recover to 0.1 If.

Note 2: Per Method 4031-A with $I_F = I_R = 200$ to 400 mA, $R_L = 100$ Ohms, recover to 0.1 If.

Note 3: Per Method 4031-A with $I_F = 10$ microA, $I_R = 1.0$ mA, recover to 0.1 mA.

Note 4: Per Method 4026 with $I_F = 200$ mA, $I_R = 1.0$ mA, recover to 0.1 mA.



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